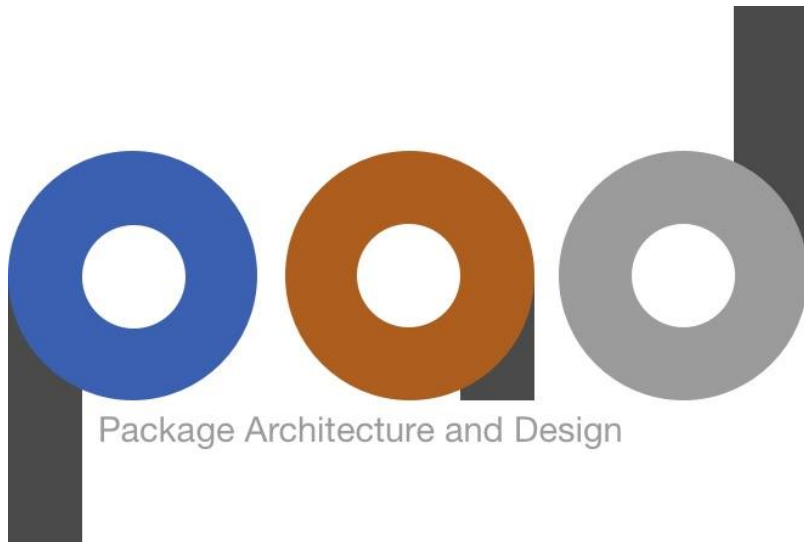


High-Level Module Design Guidelines and Design Trade-offs (Ver. 1)



- 9/10/2018
- Darko Popovic



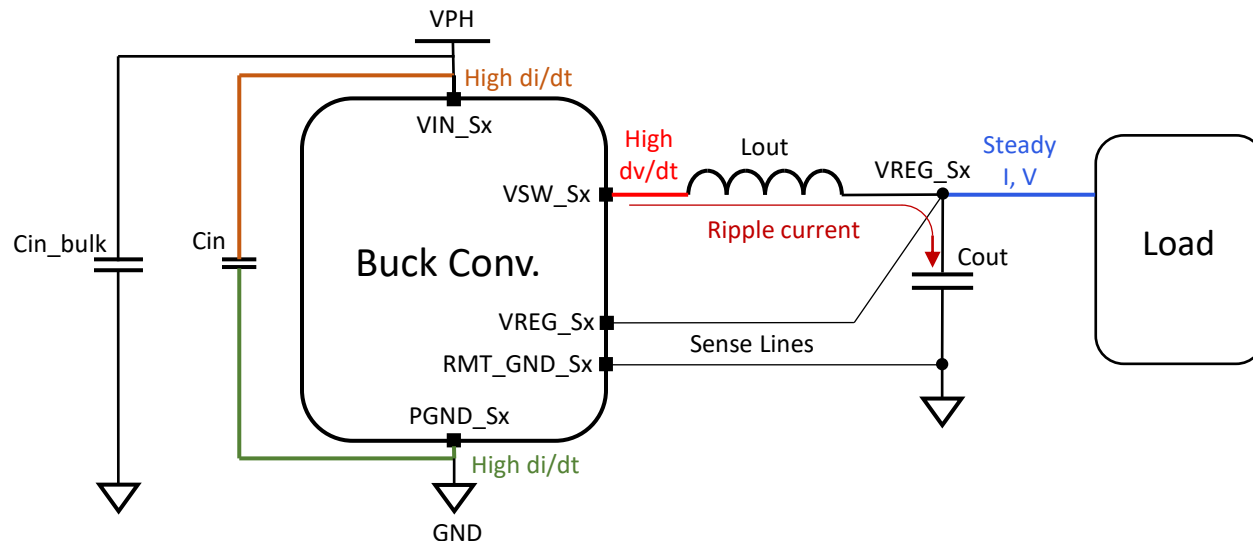
- Objective
- Links to PMIC Reference Design Documents
- High-Level Component Placement Guidelines
- High-level Design Trade-offs
- Component Placement Examples
 - Based on Wailua and MakuaA Reference Designs
- Backup

- **Provide high-level module design guidelines and design tradeoffs**
 - Includes a summary of component placement guidelines based on information provided by PMIC Systems Team
 - For comprehensive PMIC related information refer to documents on PMIC sharepoints - see the next slides for links
 - For detailed SDM information refer to BBSYS reference designs and electrical specs
 - For additional information on module design refer to [Module Design BKM](#) and other documents at Kern Module [Sharepoint](#)

- PMIC Systems Team provides Reference Design material for Qualcomm PMICs
- Each PMIC has a Sharepoint which contains: PCB layout requirements checklist, PCB layout example, reference design guide, etc.
- PMIC Reference Design Guide/Checklist should be followed wherever possible, especially for the “High Priority” requirements
- This should start with the component placement and layer assignments
- Wailua Reference Design documents can be found at: <http://go/refPM855>
- Included in Wailua Sharepoint are:
 - Checklist: “PMIC_PCB_Layout_Requirements_Wailua.xlsx”
 - Reference Design Layout Guide: “PM855_ReferenceDesign.pdf”
 - PA109_a_LDA design: “Archived_Design_Folder_PA109.zip”
- Similarly, MakuaL and MakuaA Reference Design documents can be found at:
 - <http://go/refPM855L>
 - <http://go/refPM855A>
- For VPH electrical targets refer to: <http://go/vphspecs>
- For links to TDOS, MDOS, Power Grid and more go to: <http://go/wailua>
- For PMIC Support Team FAQ and introductory technical/training material refer to: <http://go/PST>

• Buck Converters

- **Inductor** - place close to PMIC
 - **VSW_S* nets are noisy** (high dv/dt)
 - Keep sensitive signals away
 - Shield VSW* nets with GND planes above/below
- **Cin** - place close to PMIC pins
 - Place **Cout** close to PMIC pins for **boost** converters
 - Place **Cin and Cout** close to PMIC pins for **BoB**
- **Cout**
 - **Ripple current** is absorbed at Cout
 - **Reduce DC Resistance** from VSW_S* to load to improve **efficiency**
- **Sense lines**
 - Noise sensitive (keep away from VSW_S*)
 - Connect to Cout (current PMIC guidelines)



• XO

- Not too close to PMIC
- Sensitive to temperature variations, noise and parasitic capacitance
- Narrow trace connections for thermal isolation
- Metal plane opening below XO for reduced thermal transfer

• Decoupling Caps

- Decoupling caps should be placed close to load to minimize loop inductance
- In many cases optimal placement of decoupling capacitors is directly below corresponding SDM power pins (or as close as possible)
- **22uF 3T caps** may serve two functions:
 - Buck output caps
 - SDM decoupling caps

• Main GND Plane

- Low impedance main GND plane is critical for good electrical performance
- Limit plane perforation due to via antipads
- Do not route signals on main GND plane

• VPH Plane

- Low impedance plane and good connection to board is required
- Refer to **module specific VPH electrical specs** at: <http://go/vphspecs>

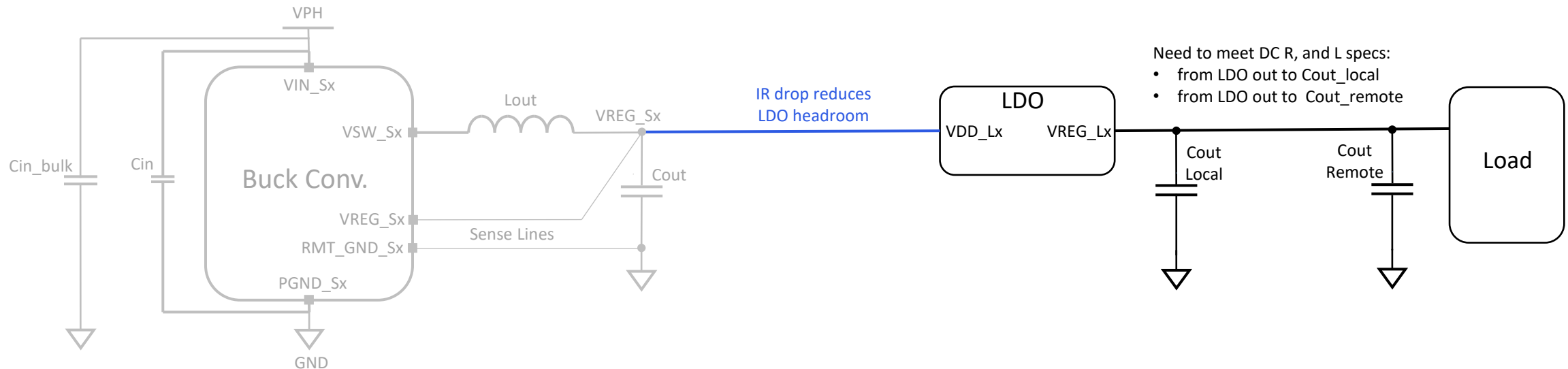
- **LDO** (Low Drop-Out Voltage Regulator)

- **Input**

- DC R between buck output at sense point and LDO input is not compensated
 - Voltage drop reduces LDO headroom, which degrades performance (PSRR, load regulation)
 - NMOS and LV PMOS LDO input is connected to buck output as shown in simplified block diagram below. MV PMOS LDO input is connected to BOB or VPH – see MDOS document for details.

- **Output**

- **Cout Local** – place close to PMIC pin to meet DC R and L specs
 - **Cout Remote** – place close to load
 - Pseudo-capless LDOs have remote output caps only, which also serve as decoupling caps for the load
 - DC R and L specs from LDO output to remote cap need to be met (DC R spec was more challenging to meet in Kern module)
 - In some cases local and remote 1uF caps can be replaced with one local 2.2uF cap (adds cost)
 - Voltage drop from LDO out to load is not compensated



Design trade-offs due to single design variable change

• Dielectric Thickness ↑

- Longer vias
 - Via inductance/resistance ↑
 - Cross-talk ↑
- Plane inductance ↑
 - Increases with PWR-GND plane separation
- Transmission line impedance ↑
 - Easier to meet typical Zdiff specs

• Metal Plane Thickness ↑

- Plane DC resistance ↓
- Transmission line impedance ↓
 - Harder to meet typical Zdiff specs

• Number of Layers ↑

- DC Resistance ↓
 - More routing area, wider trace/shape connections
- Longer top to bottom vias
 - Via inductance/resistance ↑
 - Cross-talk ↑

• Module Area ↓

- Optimal placement of decoupling capacitors ↓
 - Limited area under SDM pins
- DC Resistance ↑
 - Narrow trace/shape PWR net connections due to limited routing area
- Cross-talk ↑
 - Reduced spacing between victim nets and aggressors (components, vias and traces)

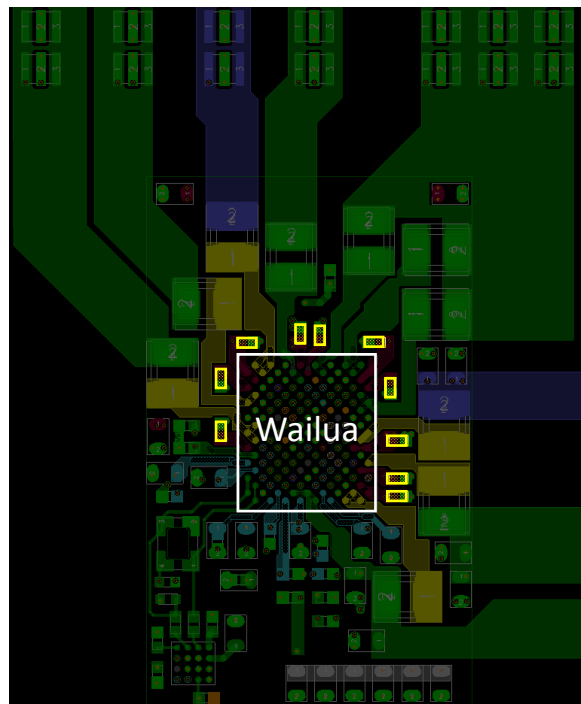
• Input:

- ↑ / ↓ - single design variable increased / decreased

• Result:

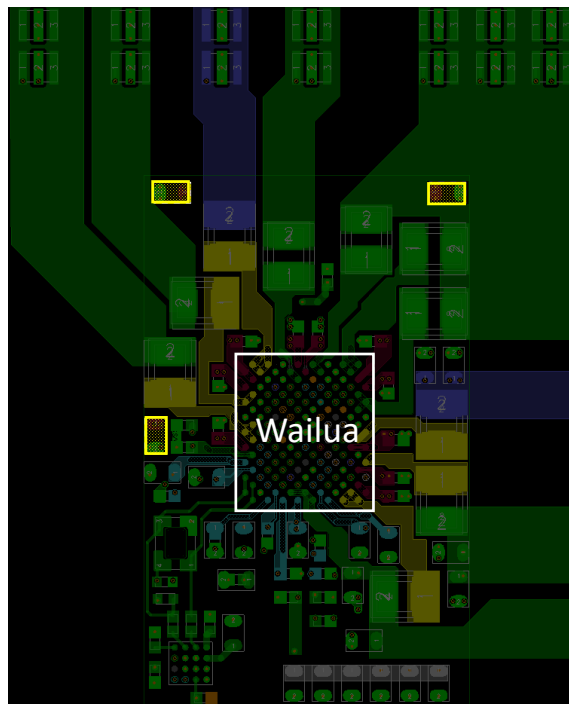
- ↑ / ↓ - parameter increased / decreased, performance improved
- ↑ / ↓ - parameter increased / decreased, performance degraded

Input Caps



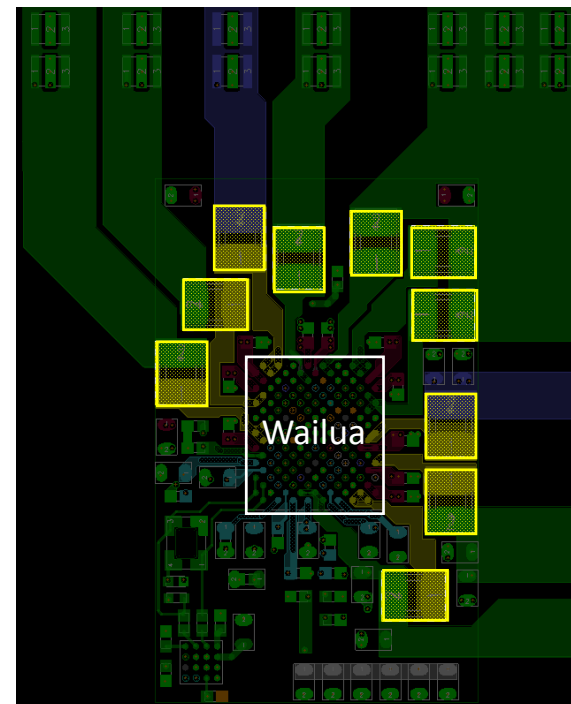
- ❑ 1uF, 0201
- ❑ One per buck with dedicated vias:
 - ❑ reduce coupling between bucks
 - ❑ reduce coupling to sensitive nets
- ❑ Place Cin close to PMIC pins to minimize loop inductance and reduce voltage spikes due to **high di/dt** at input pins

Input Caps - Bulk



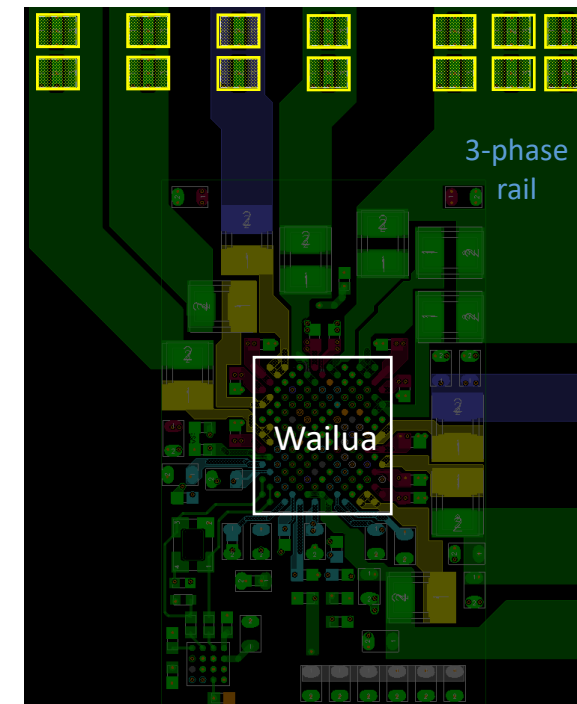
- ❑ 10uF, 0402
- ❑ ~3 per PMIC
- ❑ Can be further away from PMIC pins

Output Inductors



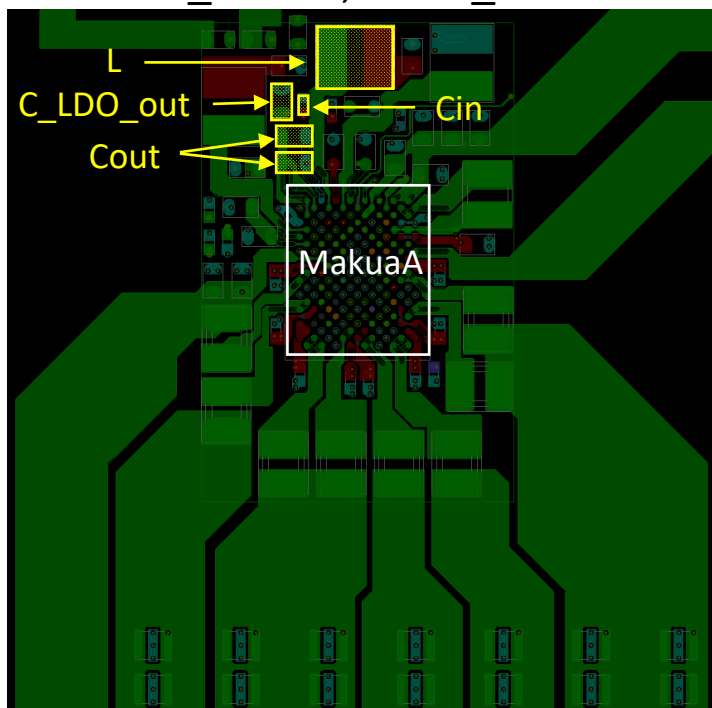
- ❑ **VSW_S*** nets between PMIC pins and inductors are **NOISY** (high dv/dt)!
 - ❑ Place Lout close to PMIC
 - ❑ Keep sensitive signals away
- ❑ 3 overlapping inductor footprints used in Wailua ref design (2016 highlighted)
- ❑ Kern module has:
 - ❑ 0.47uH, 2012, 0.8mm
 - ❑ 0.47uH, 1608, 0.8mm

Output Caps



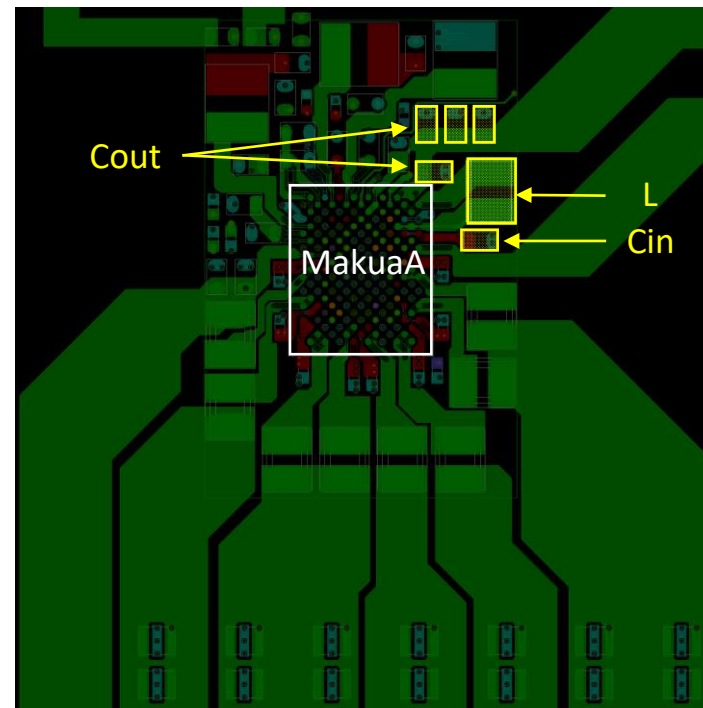
- ❑ 22uF, 3T
- ❑ 2 caps per phase
- ❑ Also serves as decoupling cap for SDM in many cases
- ❑ VREG_S* nets between inductor and output cap
- ❑ Output cap absorbs ripple current
- ❑ Reduce DC R between PMIC output and load to improve efficiency

VSW_OLEDB, VREG_OLEDB



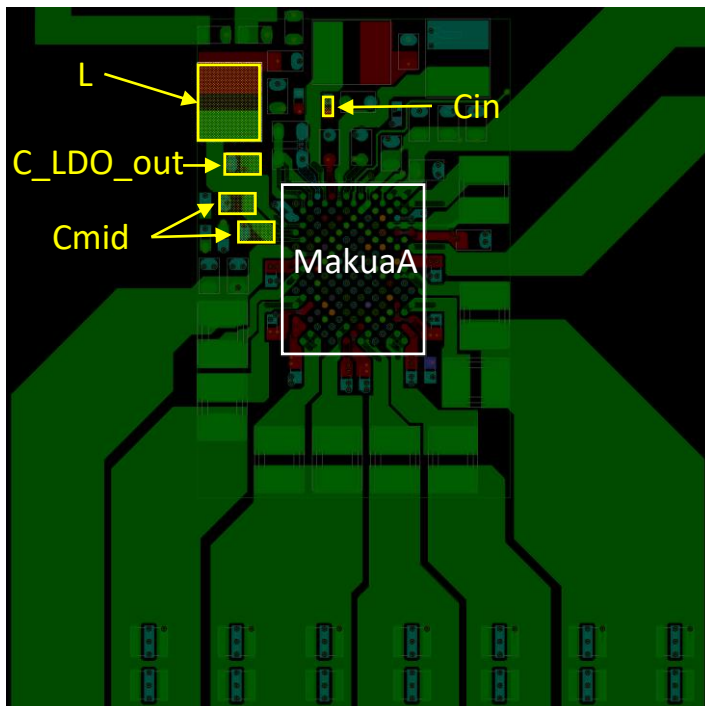
- ❑ **Cout** (10uF, 0402), close to PMIC pins VREG_OLEDB
 - ❑ Second Cout can be further from PMIC
- ❑ **PGND_OLEDB** is **NOISY** – isolate from other GND domains
- ❑ **Cin** (1uF, 0201), close to PMIC pins (lower priority)
- ❑ **C_LDO_out** (10uF, 0402), close to PMIC pins LDO_OUT_OLEDB
- ❑ **VSW_OLEDB** is **NOISY** – high dv/dt
 - ❑ Place inductor (0.47uH, 2520, 0.8mm) close to PMIC
 - ❑ Keep sensitive signals away

VBOB



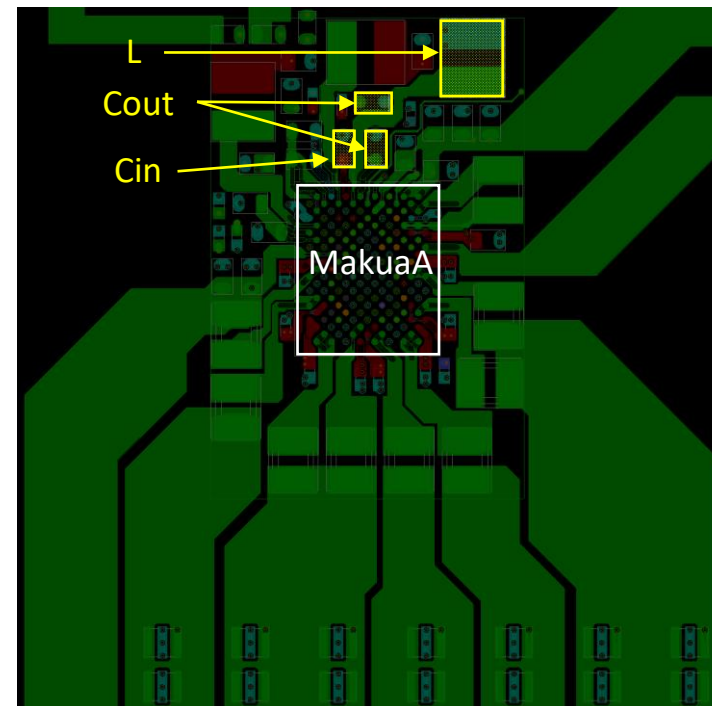
- ❑ **Both Cin and Cout close to PMIC pins**
 - ❑ One Cout close to PMIC, others can be further from PMIC
- ❑ **PGND_BOB** is **NOISY** – isolate from other GND domains
- ❑ **VSW_BOB** is **NOISY** – high dv/dt
 - ❑ Place inductor (L = 0.47uH, 2012, 0.8mm in Kern) close to PMIC
 - ❑ Keep sensitive signals away

ELVDD



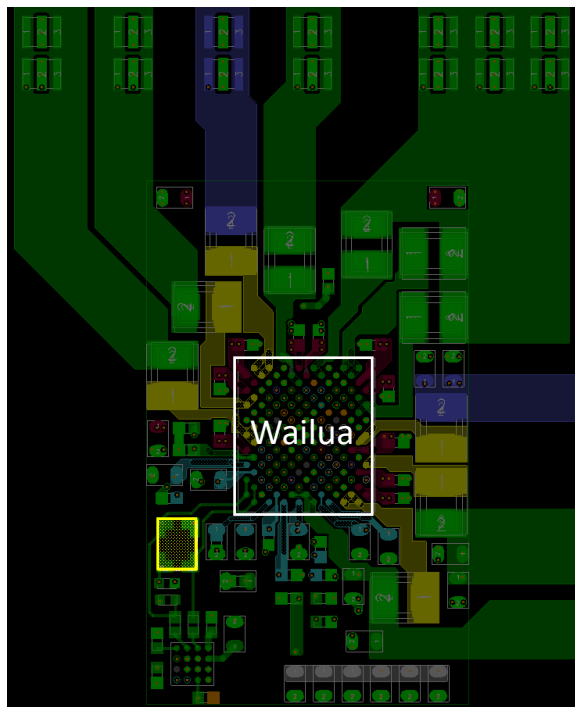
- ❑ **Cmid close to PMIC pins (MID_ELVD, LDO_IN_ELVD) - boost conv output cap**
 - ❑ Second Cmid can be further from PMIC
- ❑ **PGND_OLEDB is NOISY** – isolate from other GND domains
- ❑ **C_LDO_out** close to PMIC pins (VREG_ELVD) – LDO output cap
- ❑ **Cin** (1uF, 0201), close to PMIC pins (lower priority)
- ❑ **VSW_ELVD is NOISY** – high dv/dt
 - ❑ Place inductor (4.7uH, 2520, 0.8mm) close to PMIC
 - ❑ Keep sensitive signals away

ELVSS



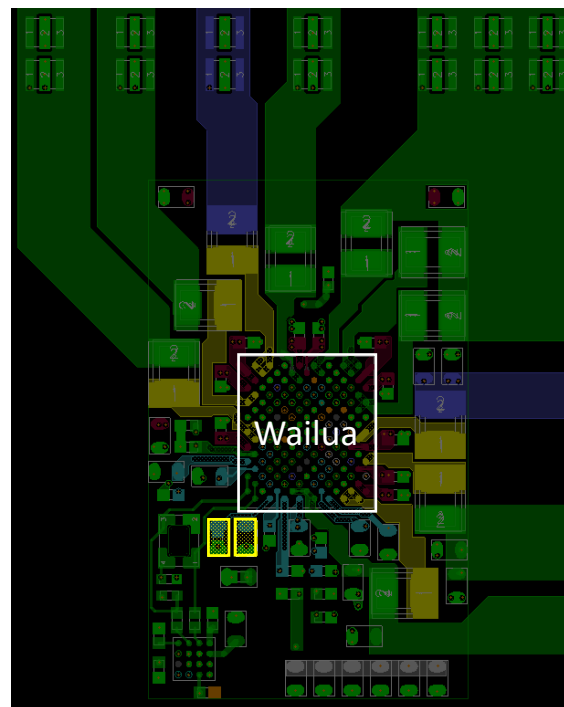
- ❑ **Both Cin and Cout close to PMIC pins**
 - ❑ Second Cout can be further from PMIC
- ❑ **VSW_ELSS is NOISY** – high dv/dt
 - ❑ Place inductor (4.7uH, 2520, 0.8mm) close to PMIC
 - ❑ Keep sensitive signals away

XO



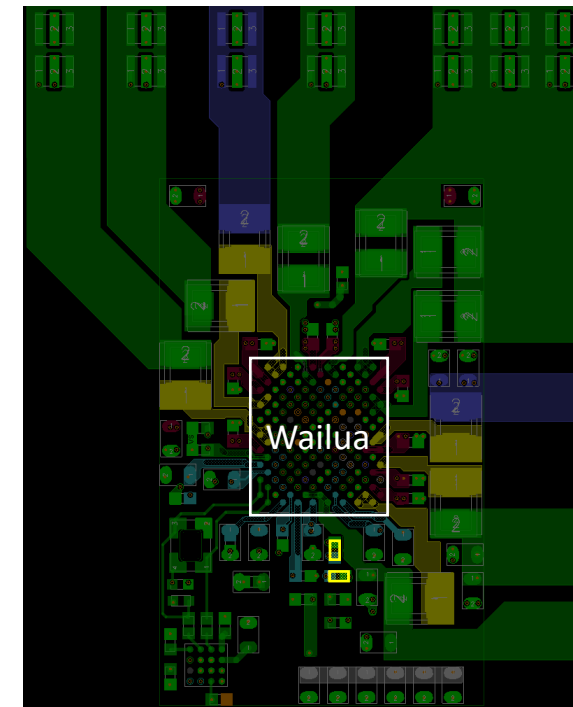
- ☐ XO not too close to PMIC
- ☐ **Sensitive to temperature variations, noise and parasitic capacitance**
 - ☐ Narrow trace connections for thermal isolation
 - ☐ Metal plane opening below XO for reduced thermal transfer
 - ☐ Dedicated vias to main GND
 - ☐ Reduce parasitic capacitance to GND and signals

VREG_XO, VREG_RF



- ☐ Short connections to PMIC pins
- ☐ Dedicated vias
- ☐ Noise sensitive

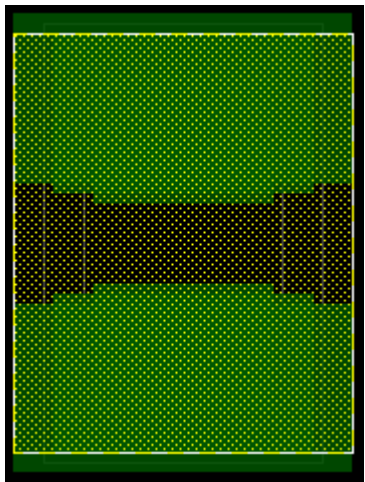
REF_BYP, AVDD_BYP



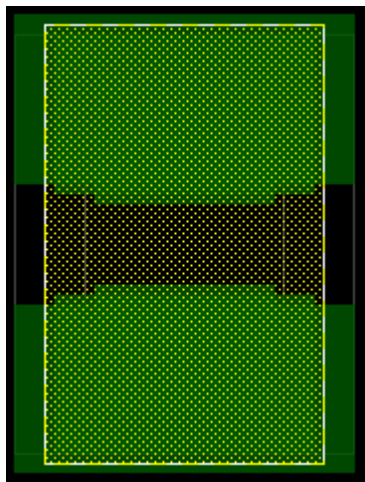
- ☐ REF_BYP, Cap 0.1uF, 0201
 - ☐ Reference voltage for PMIC
 - ☐ Noise sensitive
- ☐ AVDD_BYP, Cap 1uF, 0201
 - ☐ Voltage supply to PMIC analog circuits
 - ☐ Noise sensitive



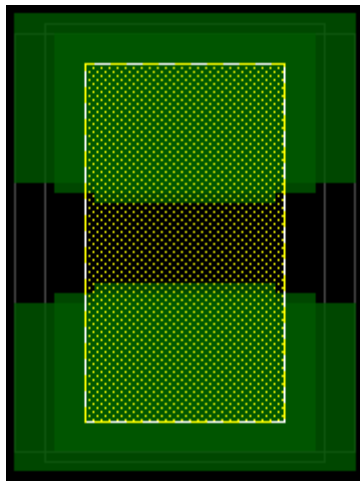
Buck Output Inductors (0.47uH) in PMIC Reference Designs



❑ 2016, 0.65mm
❑ 110-86880-0471



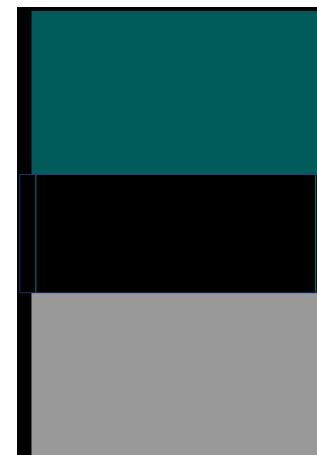
❑ 2012, 0.8mm
❑ 110-86876-0471



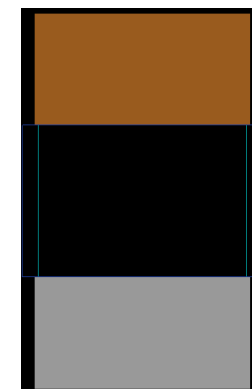
❑ 1608, 0.8mm
❑ 110-83371-0471

- PMIC Reference Designs provide options for three types of buck output inductors with overlapping footprints

Buck Output Inductors (0.47uH) in Kern Module



❑ 2012, 0.8mm
❑ 110-91600-0471



❑ 1608, 0.8mm
❑ 110-86816-0471

- Kern module has two types of buck output inductors:
 - 2012 high-current rails
 - 1608 lower current rails

Q | Metal Plane Sheet Resistance

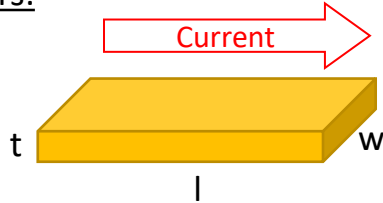
Metal plane parameters:

ρ – resistivity

t – thickness

w – width

l – length



$$R = \rho \frac{l}{S} = \rho \frac{l}{wt} = \frac{\rho}{t} \frac{l}{w}$$

Sheet Resistance: $R_s = \frac{\rho}{t}$

Number of Squares: $N_{sq} = \frac{l}{w}$

$$R = R_s \times N_{sq}$$

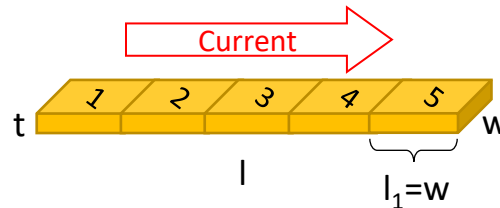
Easy way to estimate DCR

Example:

$\rho_{\text{copper}} = 1.72\text{E-}8 [\Omega\text{m}]$, $t=15\mu\text{m} \Rightarrow R_s=1.2[\text{m}\Omega/\text{sq}]$

If $N_{sq}=5$ then:

$R = 5 \text{ sq} * 1.2[\text{m}\Omega/\text{sq}] = 6[\text{m}\Omega]$



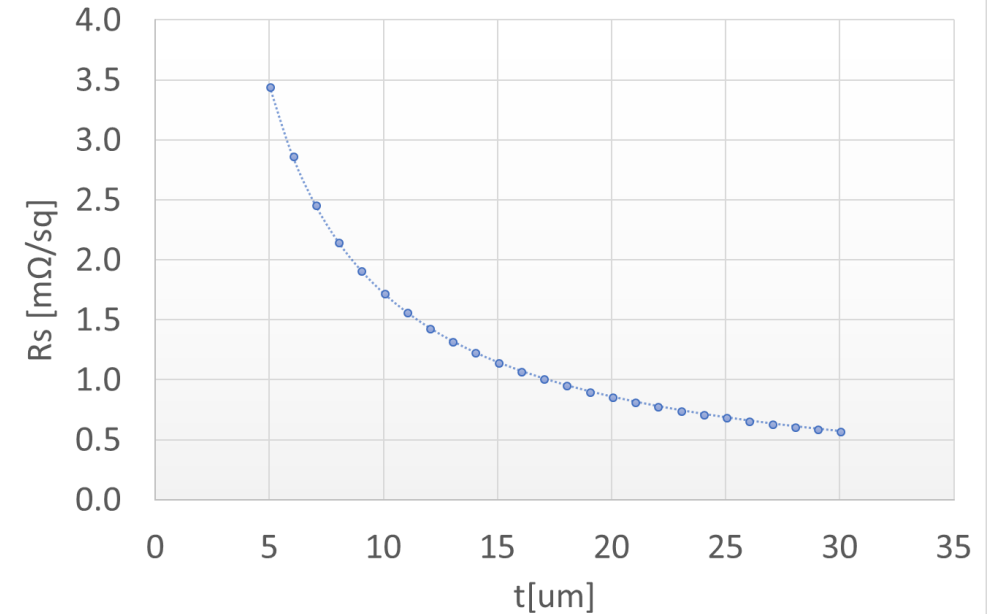
Temperature dependence (not included):

R_0 – resistance at T_0

α – temp coefficient of resistance

$$R(T) = R_0[1 + \alpha(T - T_0)]$$

Sheet resistance [$\text{m}\Omega/\text{sq}$]



Assumption: $\rho = 1.72\text{E-}8 [\Omega\text{m}]$ – copper

Metal Thickness [μm]	Sheet Resistance [mΩ/sq]	Delta relative to t=15μm [%]
5	3.4	200%
10	1.7	50%
15	1.2	
20	0.9	-25%
25	0.7	-40%
30	0.6	-50%

Kern nominal parameters shown in blue.